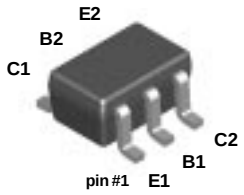
FAIRCHILD SEMICONDUCTOR™

Discrete POWER & Signal Technologies

FFB2222A FMB2222A MMPQ2222A



SC70-6
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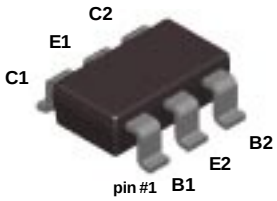

SuperSOT™-6
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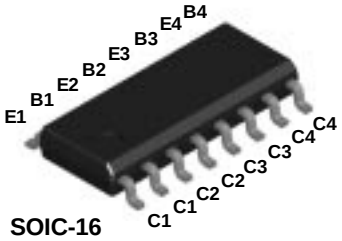


SOIC-16

NPN Multi-Chip General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19.

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2222A	FMB2222A	MMPQ2222A	
P_D	Total Device Dissipation Derate above 25°C	300 2.4	700 5.6	1,000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	415	180	 125 240	°C/W °C/W °C/W

NPN Multi-Chip General Purpose Amplifier
(continued)

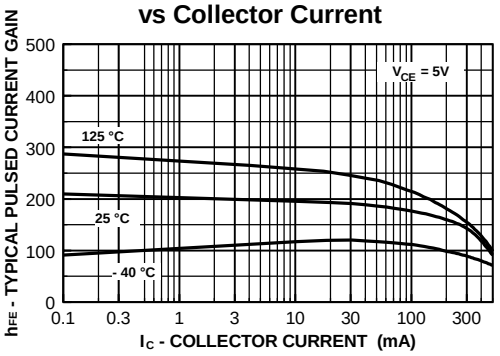
Electrical Characteristics
T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	I_C = 10 mA, I_B = 0	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	75			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	6.0			V
I_{CEX}	Collector Cutoff Current	V_{CE} = 60 V, $V_{EB(OFF)}$ = 3.0 V			10	nA
I_{CBO}	Collector Cutoff Current	V_{CB} = 60 V, I_E = 0 V_{CB} = 60 V, I_E = 0, T_A = 125°C			0.01 10	µA µA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 3.0 V, I_C = 0			10	nA
I_{BL}	Base Cutoff Current	V_{CE} = 60 V, $V_{EB(OFF)}$ = 3.0 V			20	nA
ON CHARACTERISTICS						
h_{FE}	DC Current Gain	I_C = 0.1 mA, V_{CE} = 10 V I_C = 1.0 mA, V_{CE} = 10 V I_C = 10 mA, V_{CE} = 10 V I_C= 10 mA,V_{CE}= 10 V,T_A= -55°C I_C = 150 mA, V_{CE} = 10 V* I_C = 150 mA, V_{CE} = 1.0 V* I_C = 500 mA, V_{CE} = 10 V*	35 50 75 35 100 50 40		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	I_C = 150 mA, I_B = 15 mA I_C = 500 mA, I_B = 50 mA			0.3 1.0	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	I_C = 150 mA, I_B = 1.0 mA I_C = 500 mA, I_B = 50 mA	0.6		1.2 2.0	V V
SMALL SIGNAL CHARACTERISTICS						
f_T	Current Gain - Bandwidth Product	I_C = 20 mA, V_{CE} = 20 V, f = 100 MHz		300		MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 100 kHz		4.0		pF
C_{ibo}	Input Capacitance	V_{EB} = 0.5 V, I_C = 0, f = 100 kHz		20		pF
NF	Noise Figure	I_C = 100 µA, V_{CE} = 10 V, R_S = 1.0 kΩ, f = 1.0 kHz		2.0		dB
SWITCHING CHARACTERISTICS						
t_d	Delay Time	V_{CC} = 30 V, $V_{BE(OFF)}$ = 0.5 V,		8		ns
t_r	Rise Time	I_C = 150 mA, I_{B1} = 15 mA		20		ns
t_s	Storage Time	V_{CC} = 30 V, I_C = 150 mA,		180		ns
t_f	Fall Time	I_{B1} = I_{B2} = 15 mA		40		ns

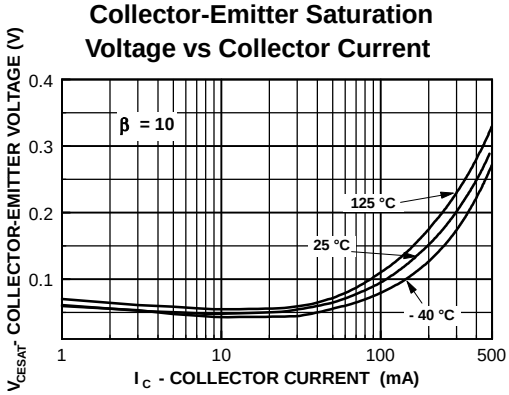
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Typical Characteristics

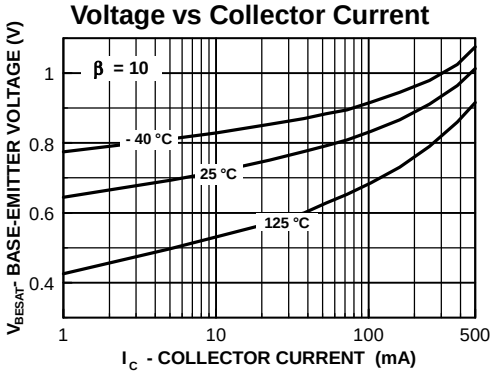
Typical Pulsed Current Gain vs Collector Current



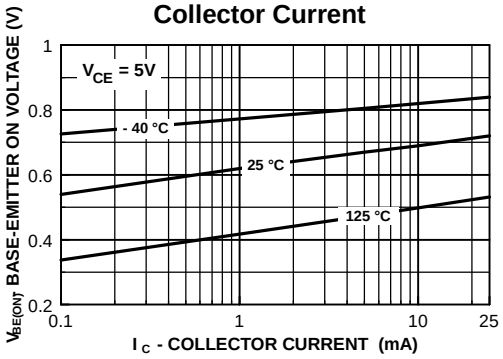
Collector-Emitter Saturation Voltage vs Collector Current



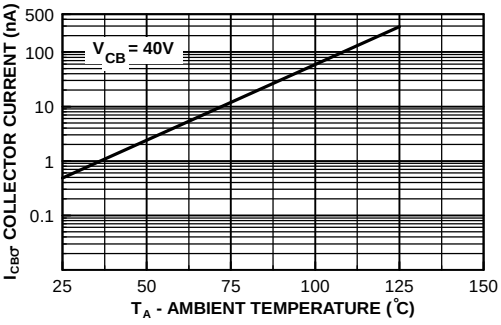
Base-Emitter Saturation Voltage vs Collector Current



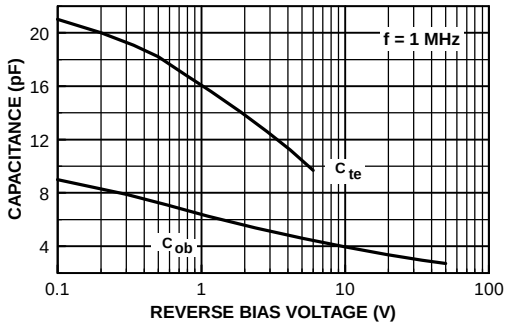
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

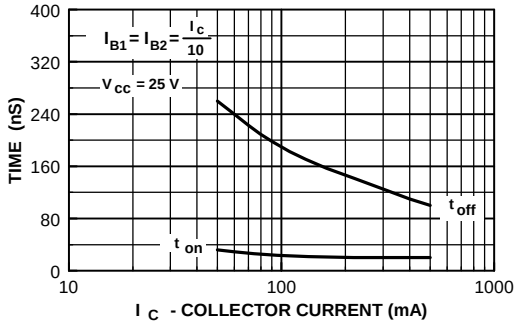


Emitter Transition and Output Capacitance vs Reverse Bias Voltage

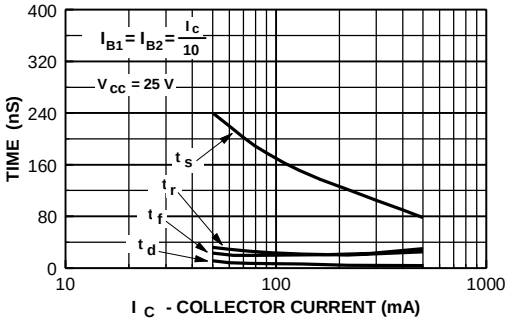


Typical Characteristics (continued)

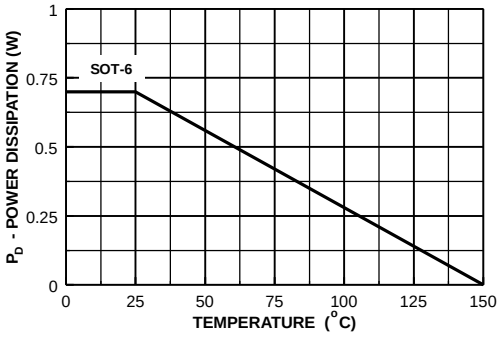
Turn On and Turn Off Times vs Collector Current



Switching Times vs Collector Current



Power Dissipation vs Ambient Temperature



Test Circuits

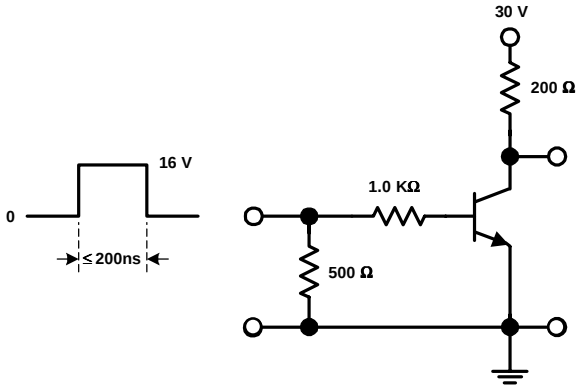


FIGURE 1: Saturated Turn-On Switching Time

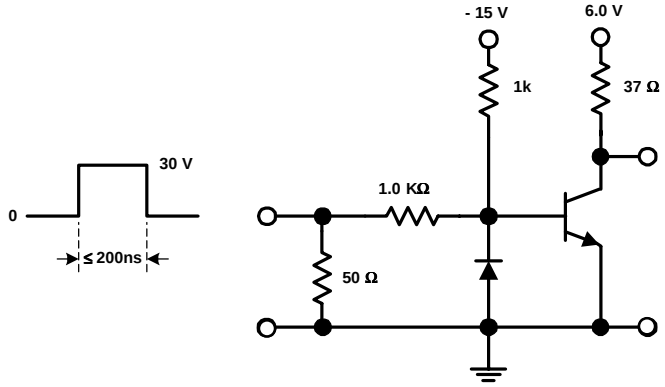


FIGURE 2: Saturated Turn-Off Switching Time